

## **PATENTS**

## INZIÉE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jack Oon Chu, et al.

**Docket: 17178** 

Patent No.: 6,890,835

**Dated: August 04, 2005** 

Issued: May 10, 2005

For: LAYER TRANSFER OF LOW DEFECT SIGE

**USING AN ETCH-BACK PROCESS** 

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## **REQUEST FOR CERTIFICATE OF CORRECTION**

Sir:

It appears that errors have been introduced in the course of printing the Patent issued in the above application, and it is respectfully requested that the Commissioner issue a Certificate of Correction in the following respects:

[57] ABSTRACT (Last Sentence)

"contact of the SiGe/Si" should read -- contact of the SiGe/Si --

Certificate
AUG 1 2 2005

of Correction

Respectfully submitted,

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## UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO

: 6,890,835 B

APPLICATION NO: 09/692,606

ISSUE DATE

: May 10, 2005

INVENTOR(S)

: Jack Oon Chu, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

[57] ABSTRACT (Last Sentence)

"contact of the SiGe/Si" should read -- contact of the SiGe/Si --

MAILING ADDRESS OF SENDER:

PATENT NO. 6,890,835

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